

FIG. 1

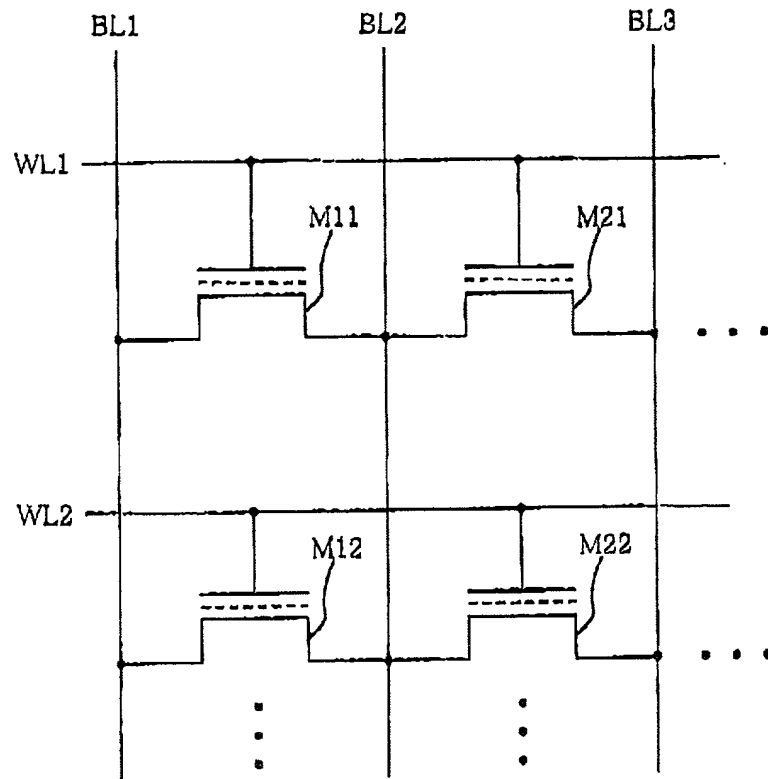


FIG. 2 is a schematic diagram of a memory cell array. The array consists of four columns of memory cells, labeled MBL1, MBL2, MBL3, and MBL4. Each column contains four memory cells, labeled BL1, BL2, BL3, and BL4. The memory cells are arranged in a grid pattern, with the columns and rows intersecting to form the cells. The columns are labeled MBL1, MBL2, MBL3, and MBL4, and the rows are labeled BL1, BL2, BL3, and BL4. The memory cells are represented by shaded rectangular areas. The columns are labeled MBL1, MBL2, MBL3, and MBL4, and the rows are labeled BL1, BL2, BL3, and BL4. The memory cells are arranged in a grid pattern, with the columns and rows intersecting to form the cells. The columns are labeled MBL1, MBL2, MBL3, and MBL4, and the rows are labeled BL1, BL2, BL3, and BL4. The memory cells are represented by shaded rectangular areas.

FIG. 2

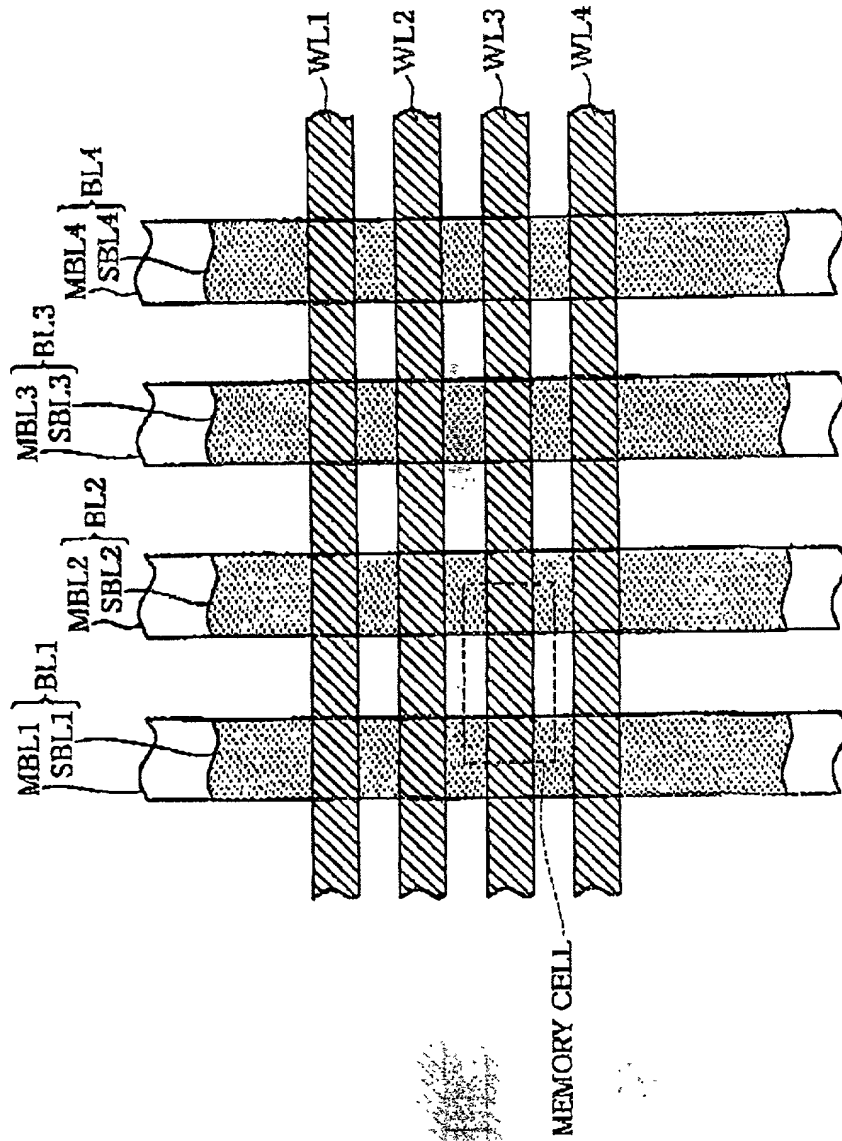
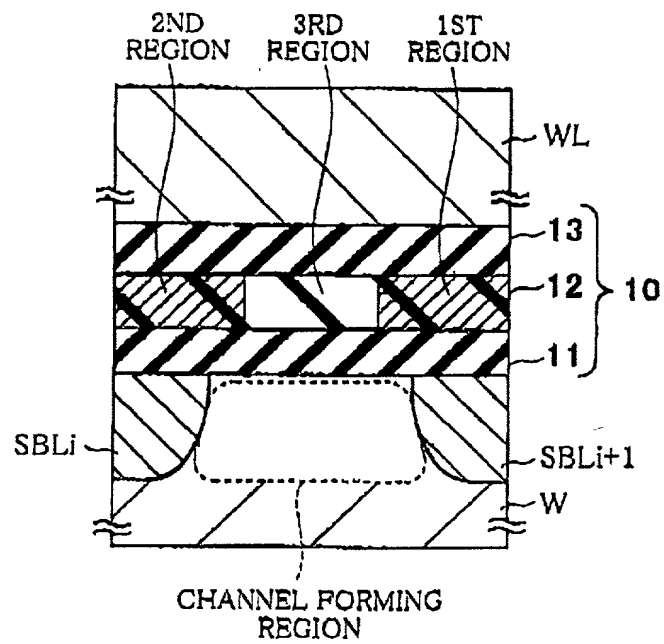


FIG. 3



# FIG. 4

## PUNCH-THROUGH CHARACTERISTICS OF MONOS TRANSISTOR

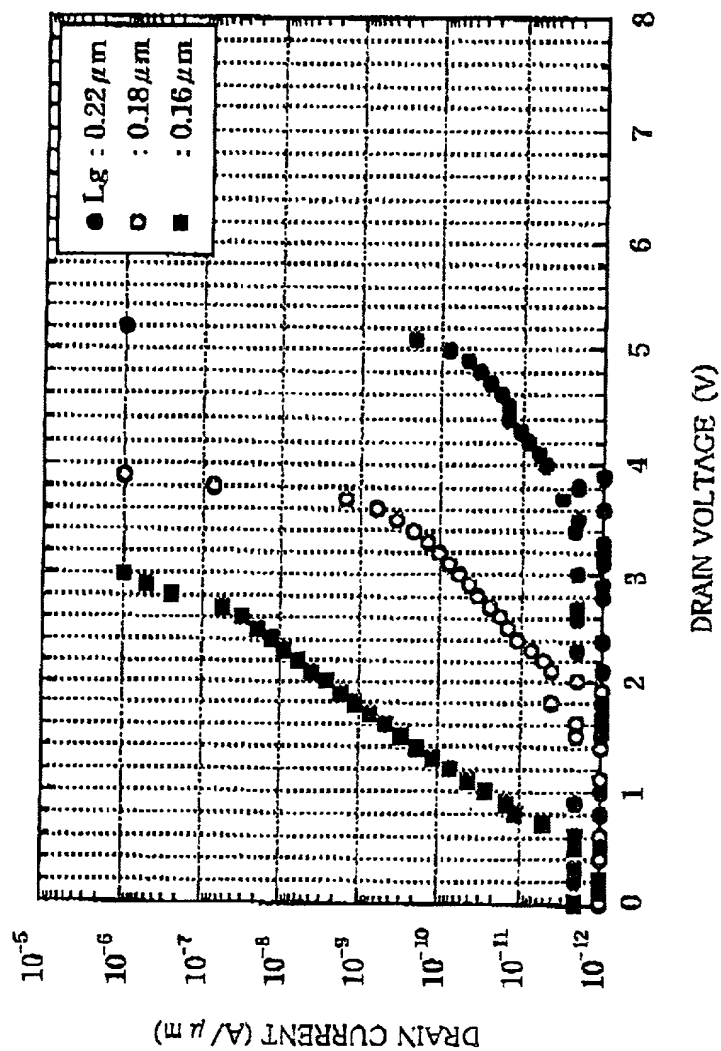


FIG. 5

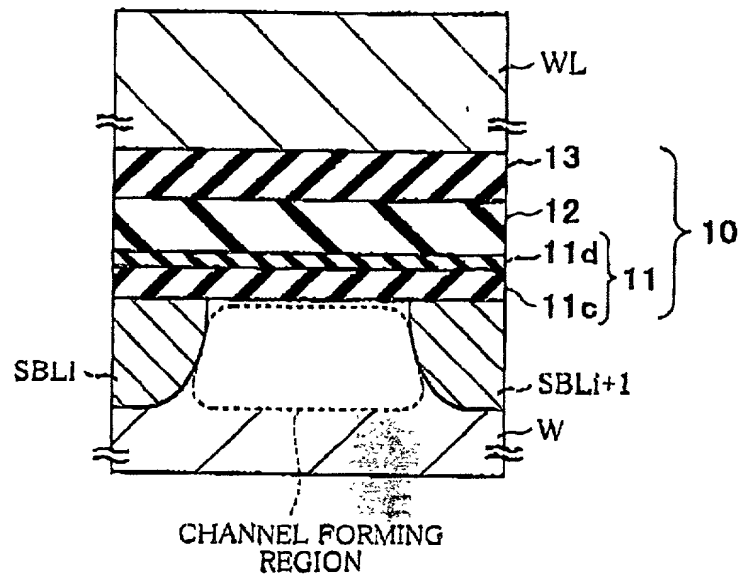


FIG. 6

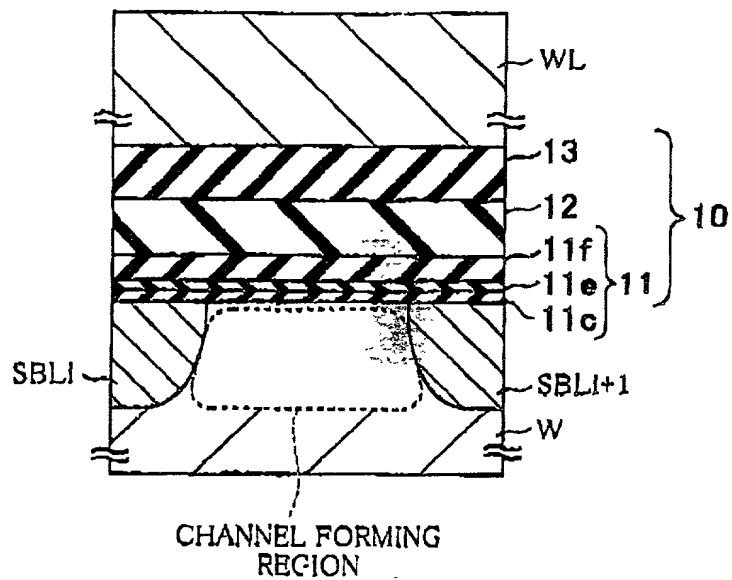


FIG. 7

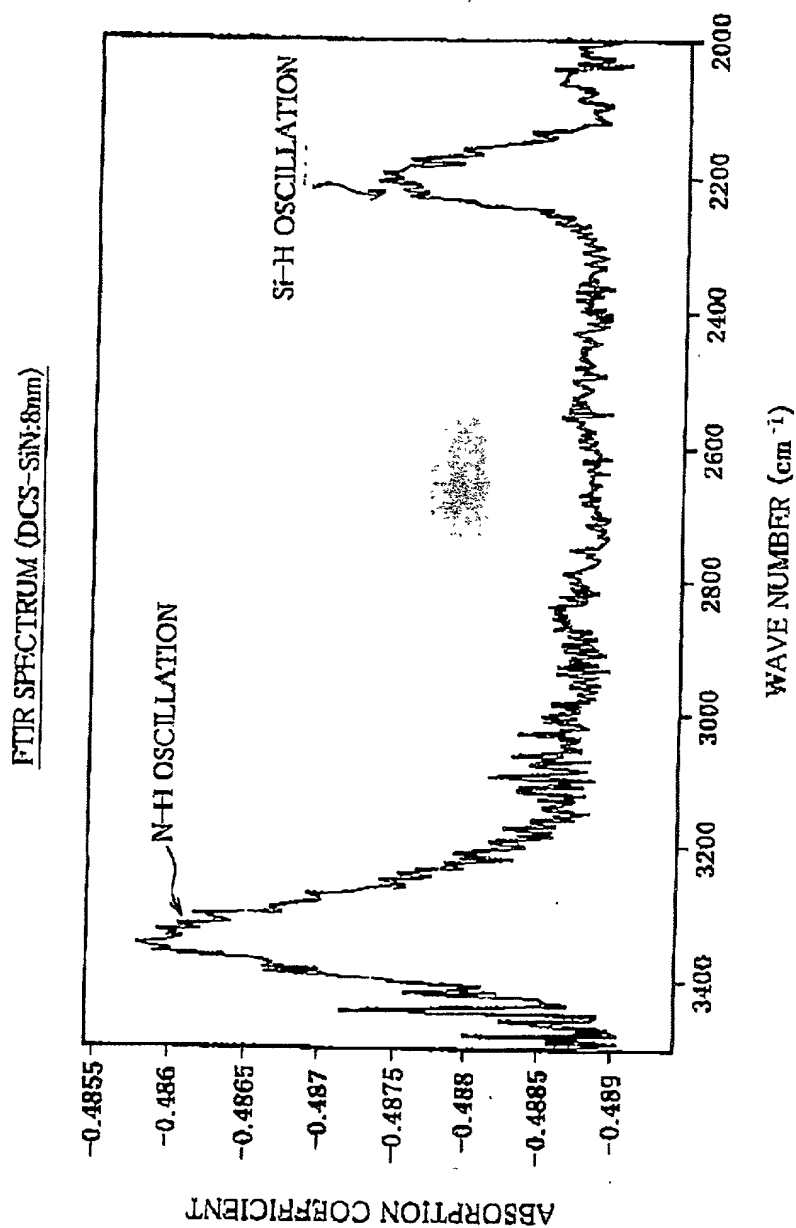
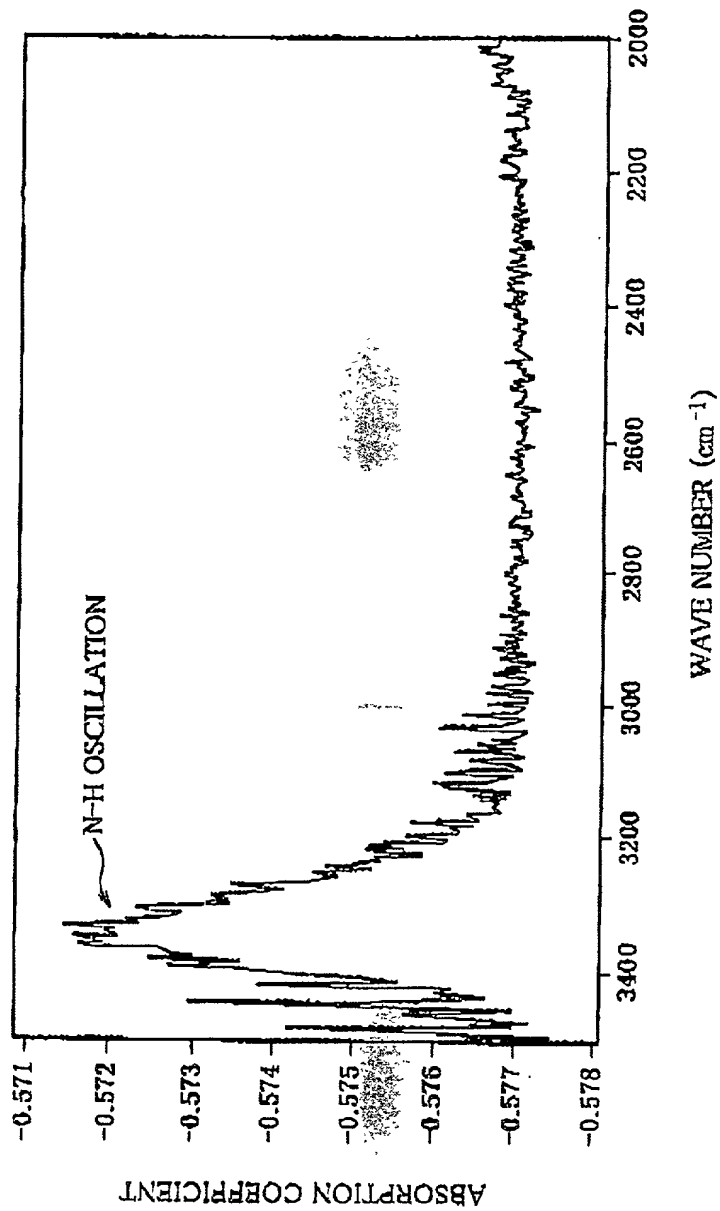


FIG. 8

FTIR SPECTRUM (TCS-SIN:8mm)



# FIG. 9

## SI-H BOND DENSITY AND N-H BOND DENSITY CALCULATED FROM THE FTIR SPECTRA

	Si-H	N-H
DCS	$1.6 \times 10^{21}$ atoms/mm <sup>3</sup>	$9.0 \times 10^{21}$ atoms/mm <sup>3</sup>
TCS	$1.1 \times 10^{20}$ atoms/mm <sup>3</sup>	$1.3 \times 10^{22}$ atoms/mm <sup>3</sup>

# FIG. 10

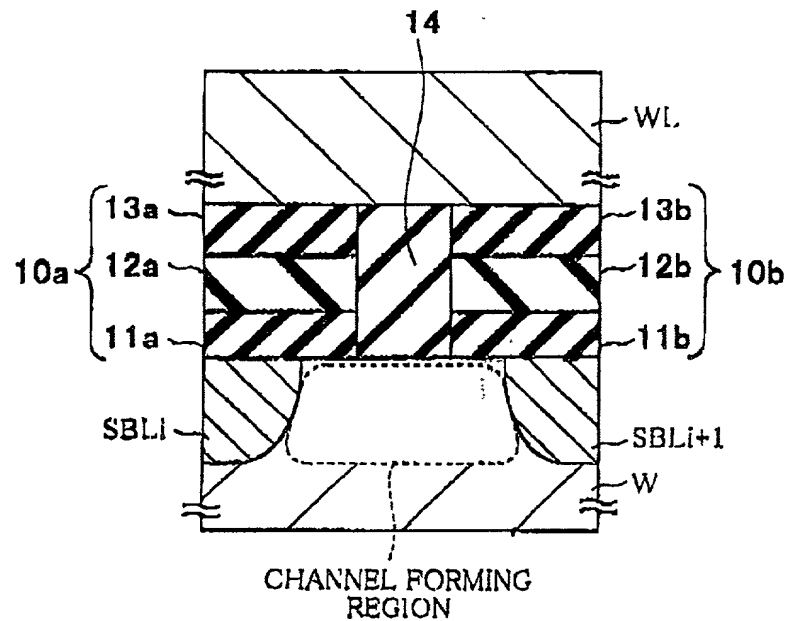




FIG. 11

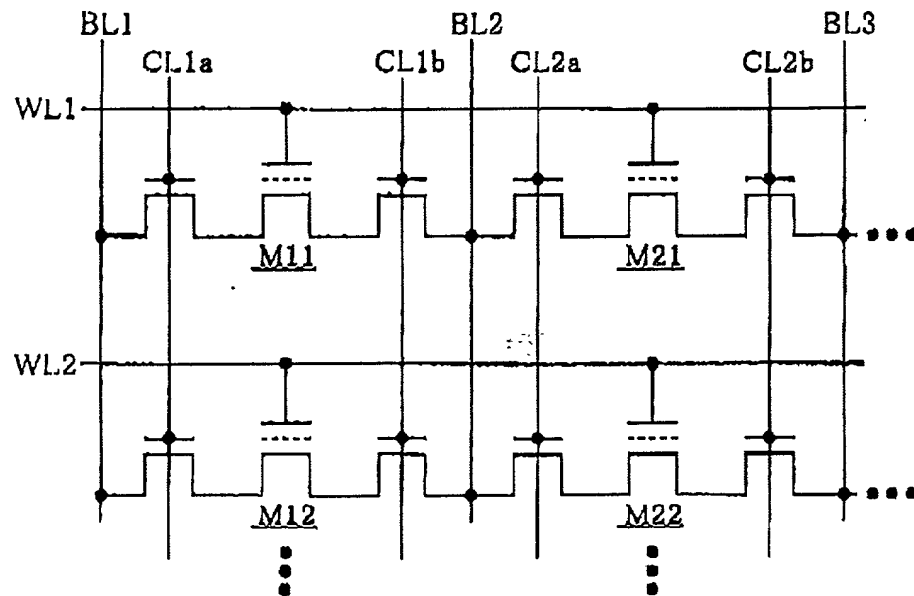


FIG. 12

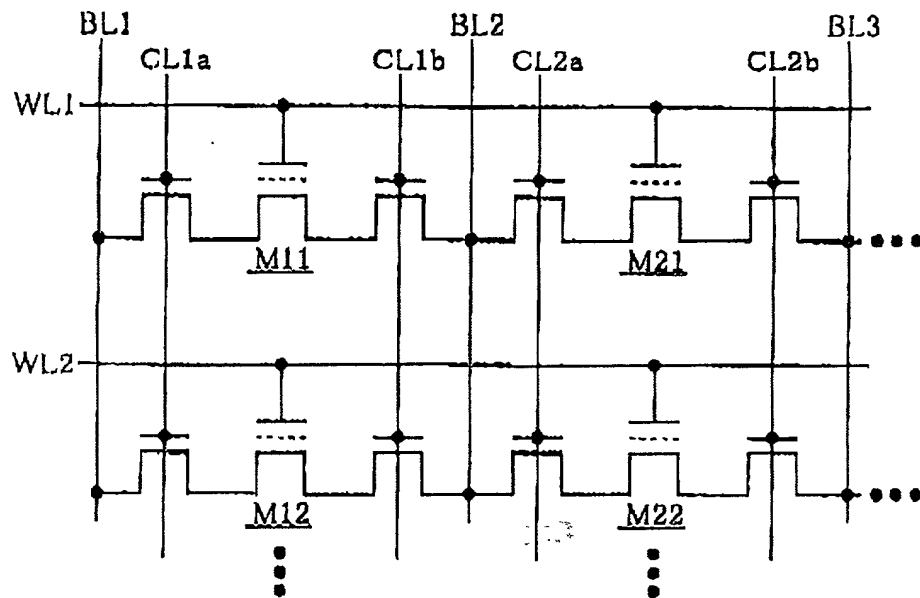
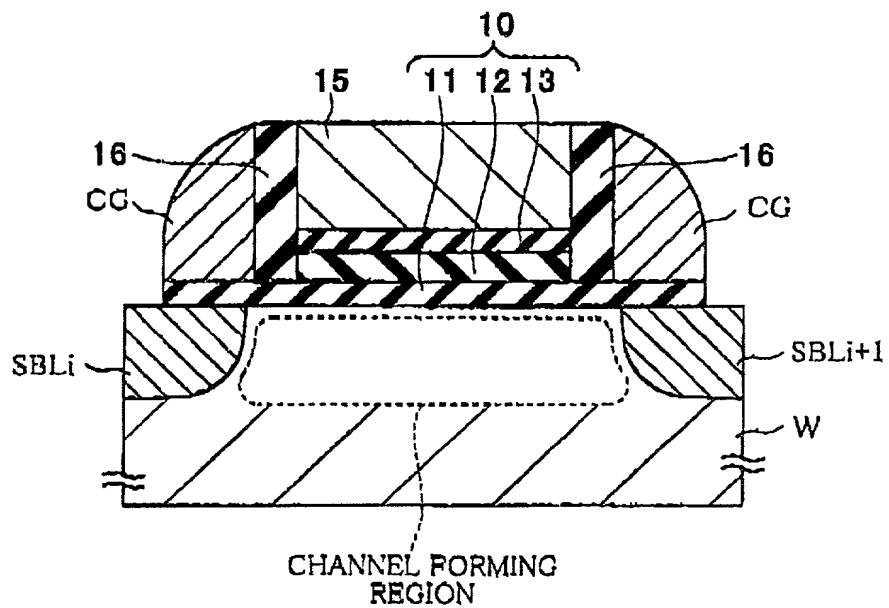


FIG. 13



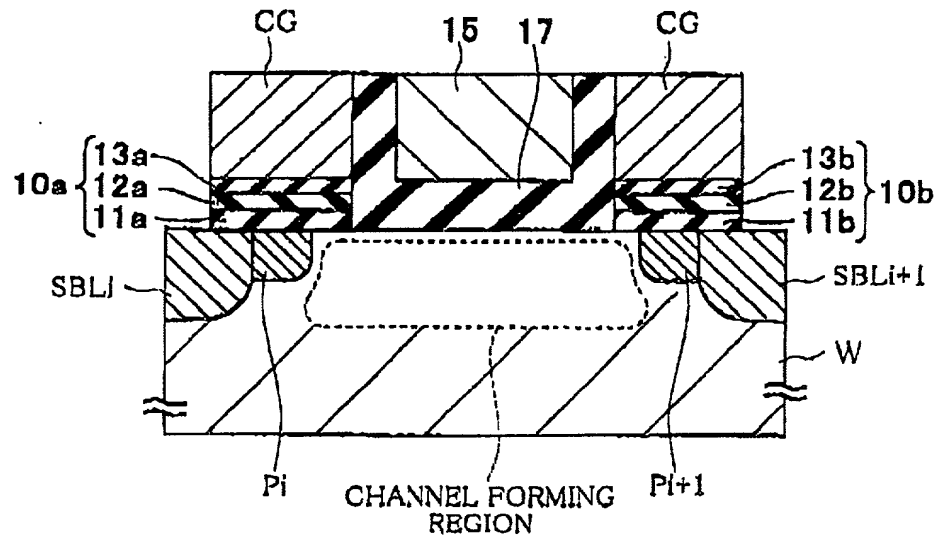
[illegible]

FIG. 15

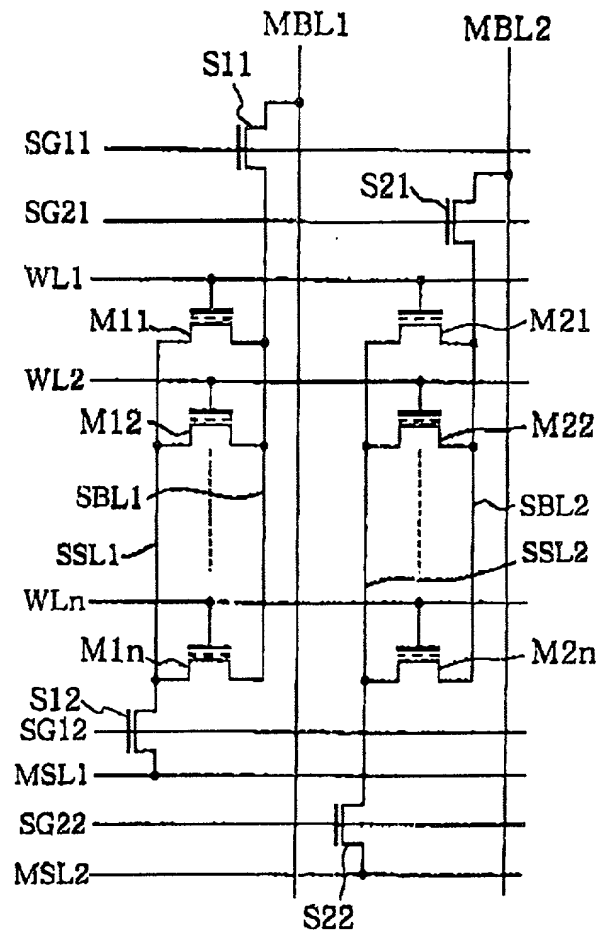


FIG. 16

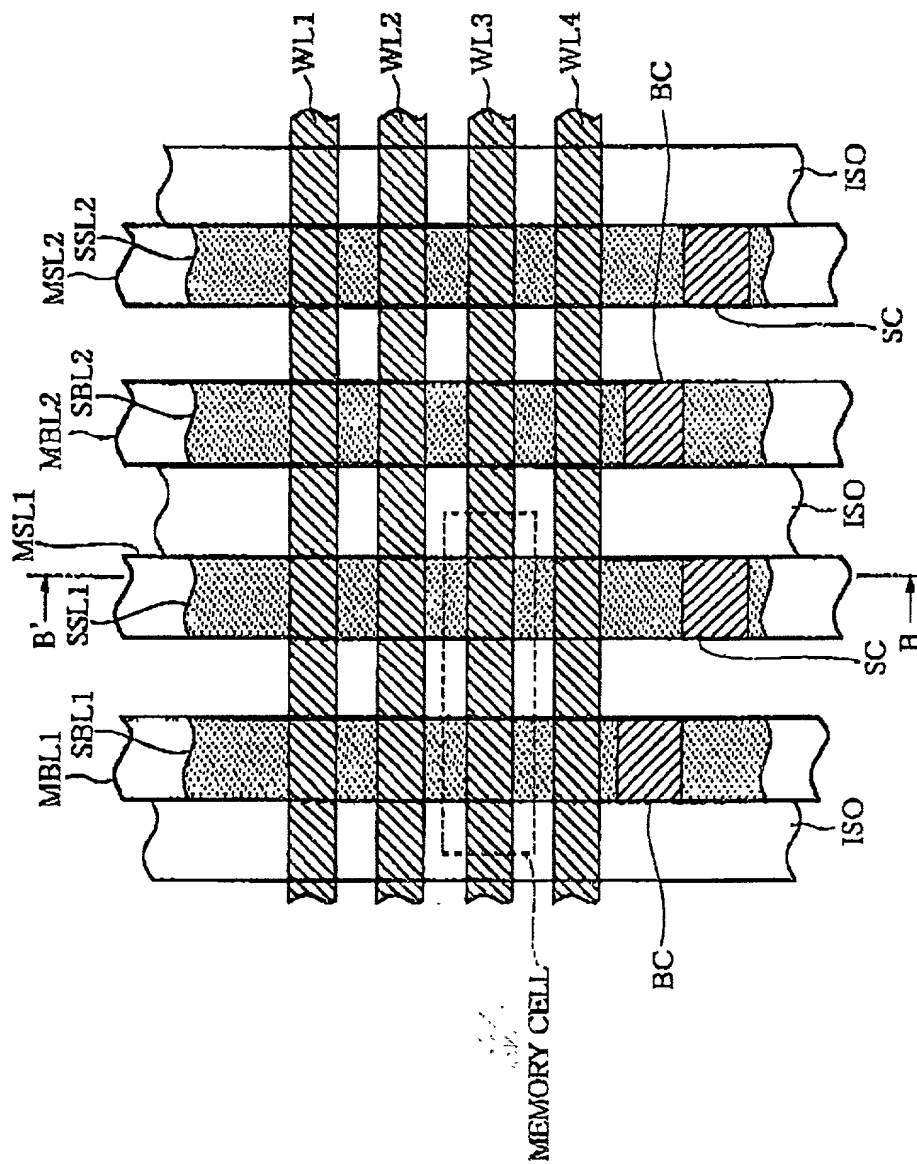


FIG. 17

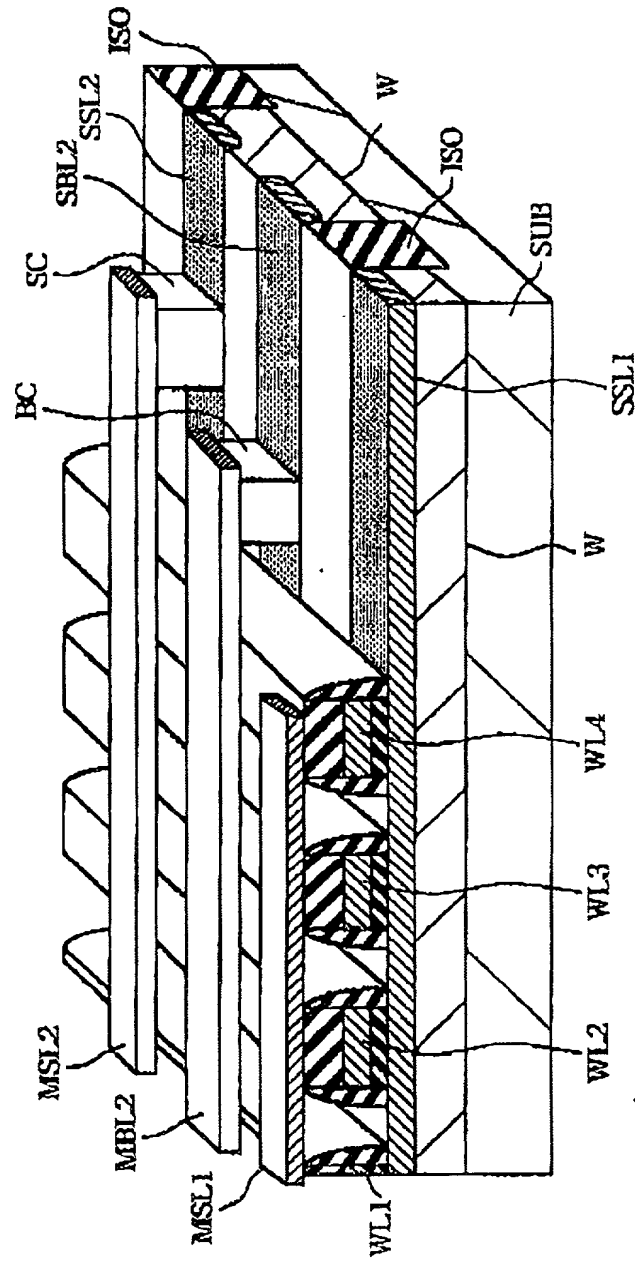


FIG. 18

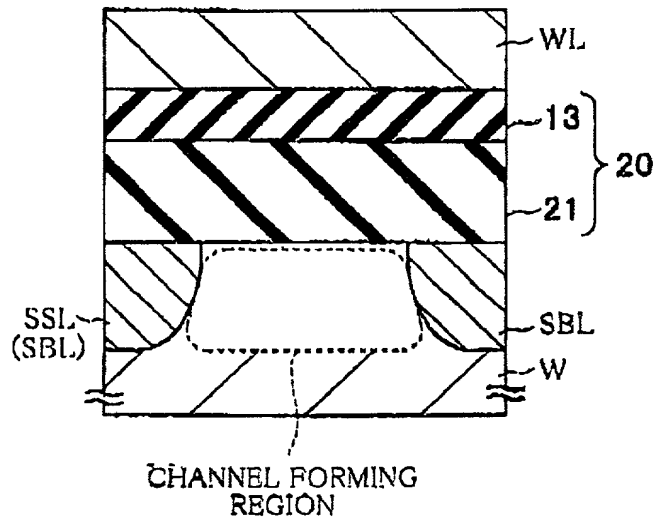


FIG. 19

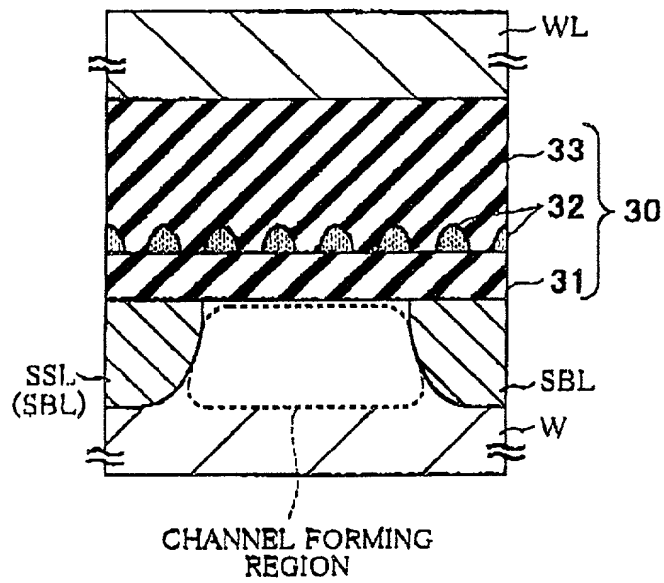


FIG. 20

